

Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.8)	V_{pp}	3	kV
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ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33\Omega$	- -	MAX.	35	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=150$ $R_L=3.3k\Omega$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	50	mA
				70	
I_H	$I_T=100mA$		MAX.	45	mA
dV/dt	$V_D=540V$ Gate Open $T_j=150$		MIN.	1000	V/ μs
$(dI/dt)_c$	$(dV/dt)_c=20V/\mu s$, $T_j=150$		MIN.	5	A/ms
t_{on}	$I_G=40mA$ $I_A=200mA$ $I_R=20mA$ $T_j=25$		TYP.	3	μs
t_{off}				30	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=11A$ $t_p=380\mu s$	$T_j=25$	1.4	V
V_{TO}	Threshold voltage	$T_j=150$	0.79	V
R_D	Dynamic resistance	$T_j=150$	51	$m\Omega$

 I_{DRM}
 $V_D=V_{DRM}$ $V_R=V_{RRM}$ V

FIG.1: Maximum power dissipation versus axim (TE)-0 T10.199.4668 0.4onM

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

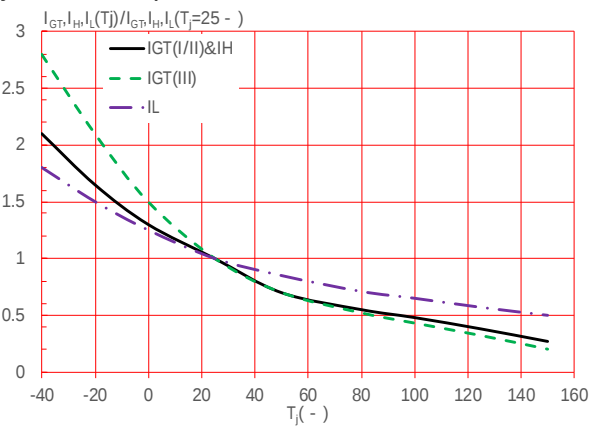
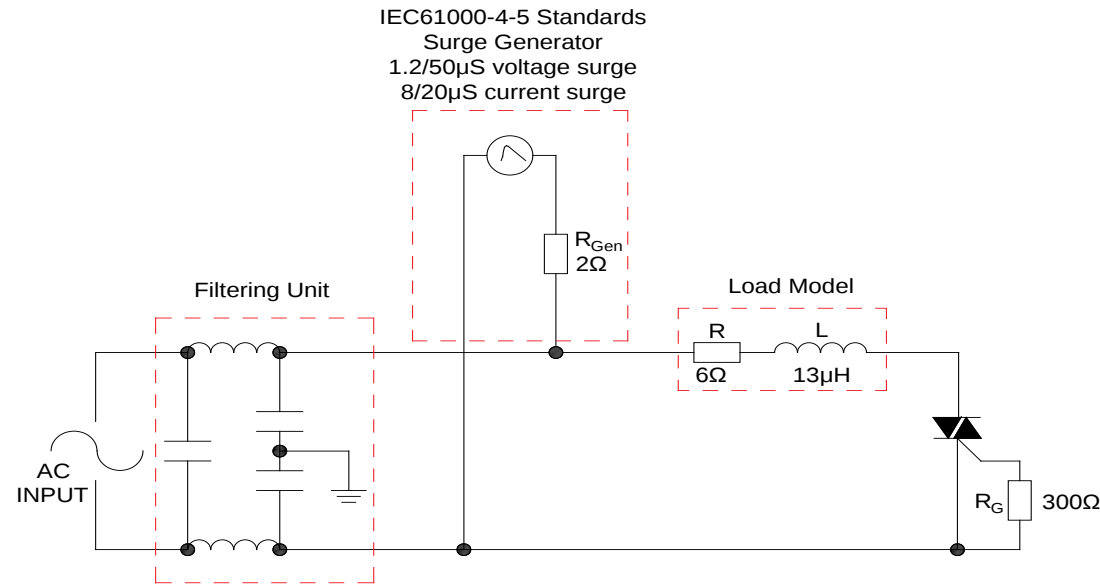
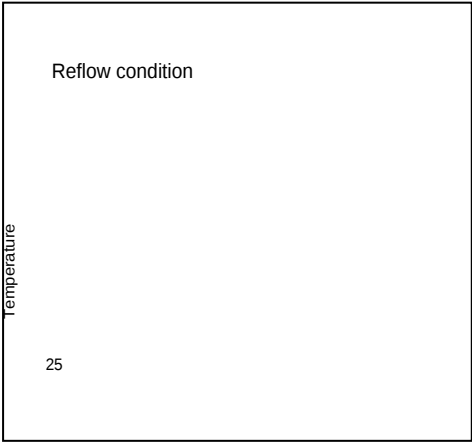


FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



SOLDERING PARAMETERS

Reflow Condition		Pb-Free assembly (see figure at right)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150
	-Temperature Max($T_{s(max)}$)	+200
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquidus Temp (T_L) to peak)		3 /sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3 /sec. Max
Reflow	-Temperature(T_L)(Liquidus)	+217
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)
Time within 5 of actual Peak Temp (t_p)		20-40secs.
Ramp-down Rate		6 /sec. Max
Time 25 to Peak Temp (T_p)		8 min. Max
Do not exceed		+260



ORDERING INFORMATION



PACKAGE MECHANICAL DATA

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90		10.20	0.390		0.402
B	14.70		15.80	0.579		0.622
C	9.40		9.60	0.370		0.378
D	2.40			0.094		
E	1.20		1.50	0.047(0)]TJ	0 Tc 0 Tw 31G	
F						

T835H-8E